

FDS4435BZ

30 Volt P-Channel PowerTrench® MOSFET

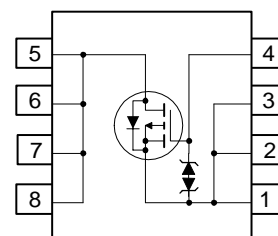
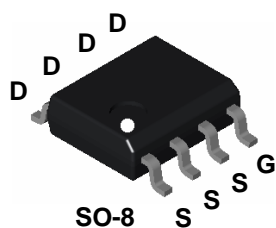
General Description

This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance.

This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

Features

- -8.8 A, -30 V. $R_{DS(ON)} = 20\text{ m}\Omega @ V_{GS} = -10\text{ V}$
 $R_{DS(ON)} = 35\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
- Extended V_{GSS} range (-25V) for battery applications
- HBM ESD protection level of $\pm 4.5\text{ kV}$ typical (note 3)
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability
- Termination is Lead-free and RoHS compliant



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	-30	V
V _{GSS}	Gate-Source Voltage	±25	V
I _D	Drain Current – Continuous (Note 1a)	-8.8	A
	– Pulsed	-50	
P _D	Power Dissipation for Single Operation (Note 1a)	2.5	W
	(Note 1b)	1.2	
	(Note 1c)	1.0	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	25	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS4435BZ	FDS4435BZ	13"	12mm	2500 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		-24		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 25\text{ V}, V_{DS} = 0\text{ V}$			± 10	μA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-1	-1.9	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -8.8\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -6.7\text{ A}$ $V_{GS} = -10\text{ V}, I_D = -8.8\text{ A}, T_J = 125^\circ\text{C}$		16 25 23	20 35 29	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -8.8\text{ A}$		24		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$		1365		pF
C_{oss}	Output Capacitance			240		pF
C_{rss}	Reverse Transfer Capacitance			200		pF

Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -15\text{ V}, I_D = -1\text{ A}, V_{GS} = -10\text{ V}, R_{GEN} = 6\ \Omega$		12	23	ns
t_r	Turn-On Rise Time			13	24	ns
$t_{d(off)}$	Turn-Off Delay Time			68	109	ns
t_f	Turn-Off Fall Time			38	61	ns
$Q_{g(TOT)}$	Total Gate Charge, $V_{GS} = 10\text{ v}$	$V_{DS} = -15\text{ V}, I_D = -8.8\text{ A}$		29.0	41	nC
$Q_{g(TOT)}$	Total Gate Charge, $V_{GS} = 5\text{ v}$			16.5	23	nC
Q_{gs}	Gate-Source Charge			4.4		nC
Q_{gd}	Gate-Drain Charge			7.3		nC

Drain-Source Diode Characteristics and Maximum Ratings

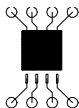
I_S	Maximum Continuous Drain-Source Diode Forward Current			-2.1	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -2.1\text{ A}$ (Note 2)		-0.76	-1.2	V
t_{RR}	Reverse Recovery Time	$I_F = -8.8\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}$ (Note 2)		24		ns
Q_{RR}	Reverse Recovery Charge			9		nC

Notes:

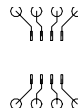
- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



- a) $50^\circ\text{C}/\text{W}$ (10 sec)
 $62.5^\circ\text{C}/\text{W}$ steady state
when mounted on a
 1 in^2 pad of 2 oz
copper



- b) $105^\circ\text{C}/\text{W}$ when
mounted on a $.04\text{ in}^2$
pad of 2 oz
copper



- c) $125^\circ\text{C}/\text{W}$ when mounted on a
minimum pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

- The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics

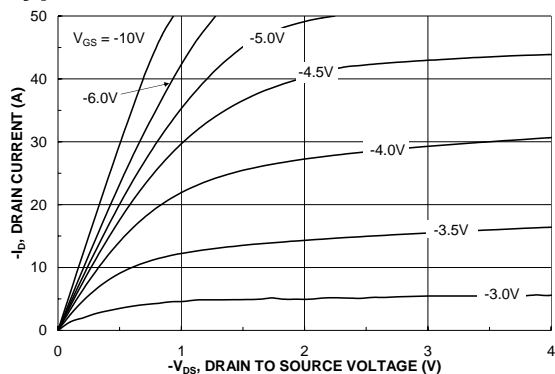


Figure 1. On-Region Characteristics.

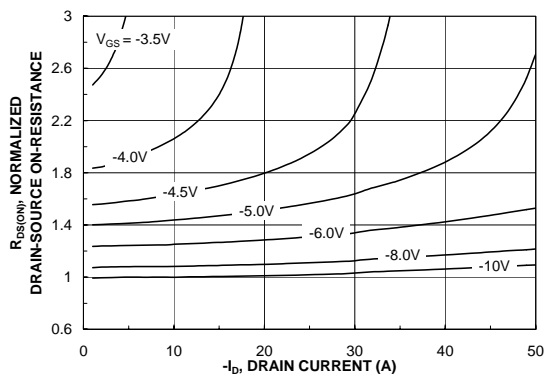


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

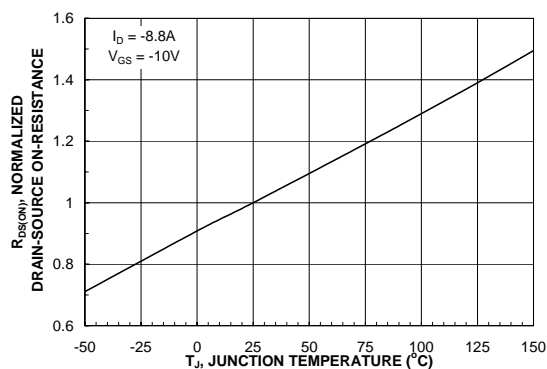


Figure 3. On-Resistance Variation with Temperature.

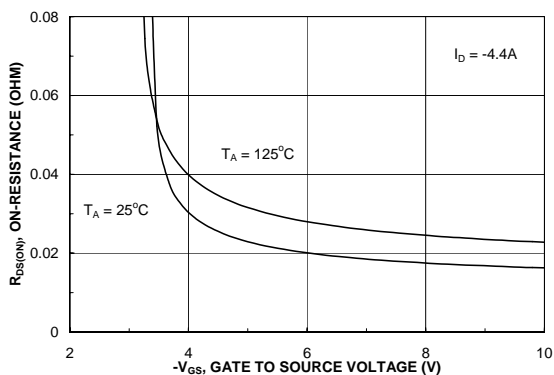


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

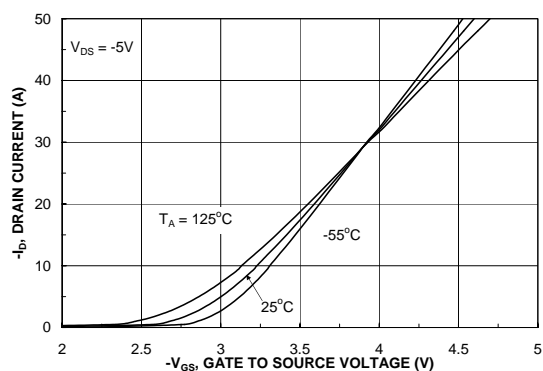


Figure 5. Transfer Characteristics.

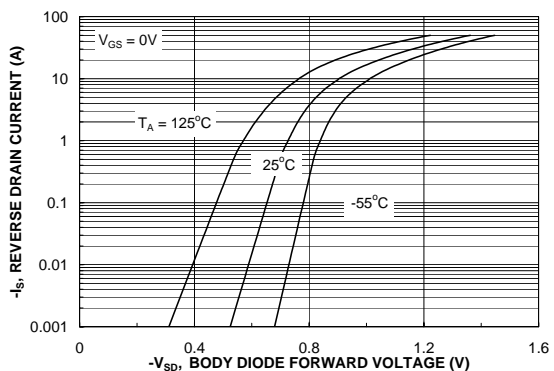


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

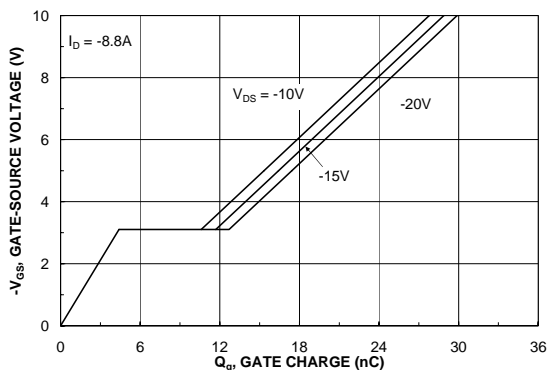


Figure 7. Gate Charge Characteristics.

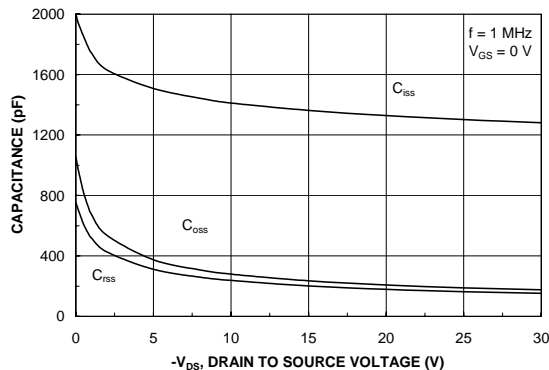


Figure 8. Capacitance Characteristics.

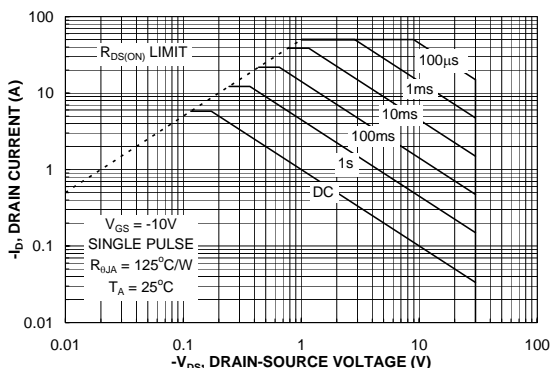


Figure 9. Maximum Safe Operating Area.

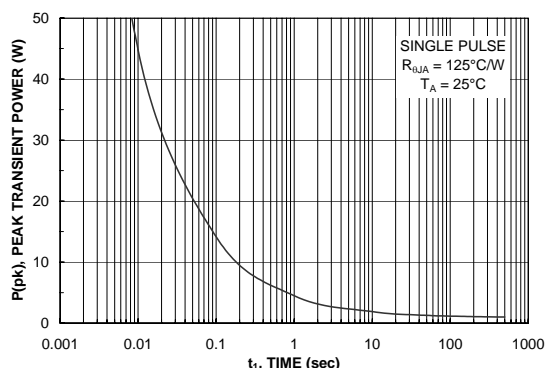


Figure 10. Single Pulse Maximum Power Dissipation.

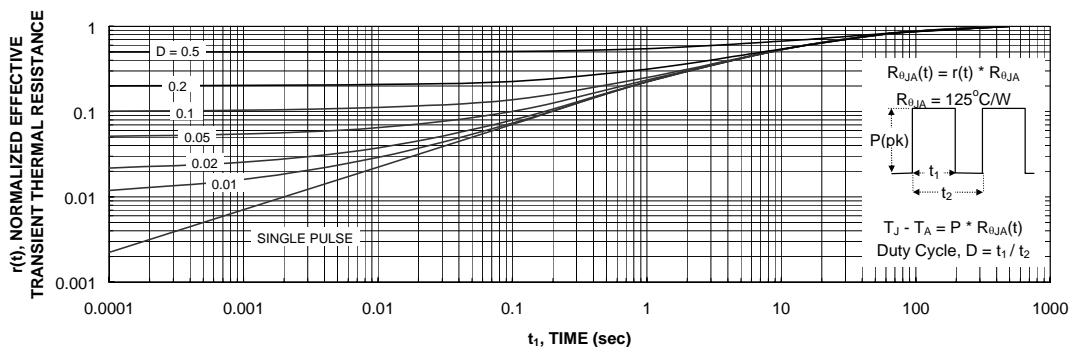


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.